



# **DZT851**

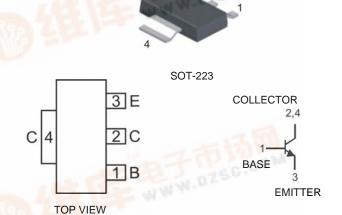
### NPN SURFACE MOUNT TRANSISTOR

#### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DZT951)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	150	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	Ic	6	А
Power Dissipation	P <sub>tot</sub>	1(Note 3) 3(Note 4)	W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

No purposefully added lead. Notes:

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

Device mounted on FR-4 PCB, pad layout as shown on page 4.

The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.





#### **Electrical Characteristics** $@T_A = 25^{\circ}C$ unless otherwise specified

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	150	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	60		_	V	$I_C = 10 \text{mA*}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6		_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	_	50 1	nA μA	$V_{CB} = 120V, I_{E} = 0$ $V_{CB} = 120V, I_{E} = 0, T_{A} = 100^{\circ}C$
Emitter Cutoff Current	I <sub>EBO</sub>	_		10	nA	$V_{EB} = 6V, I_{C} = 0$
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	— — —		50 100 170 375	mV	$\begin{split} I_C &= 0.1A,\ I_B = 5mA^* \\ I_C &= 1A,\ I_B = 50mA^* \\ I_C &= 2A,\ I_B = 50mA^* \\ I_C &= 6A,\ I_B = 300mA^* \end{split}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	1200	mV	$I_C = 6A$ , $I_B = 300 \text{mA}^*$
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>	_	_	1150	mV	$I_{CE} = 6A, V_{CE} = 1V^*$
DC Current Gain	h <sub>FE</sub>	100 100 75 25		300 —		$\begin{split} I_C &= 10 \text{mA},  V_{CE} = 1 \text{V}^* \\ I_C &= 2 \text{A},  V_{CE} = 1 \text{V}^* \\ I_C &= 5 \text{A},  V_{CE} = 1 \text{V}^* \\ I_C &= 10 \text{A},  V_{CE} = 1 \text{V}^* \end{split}$
SMALL SIGNAL CHARACTERISTICS	•		•	•	•	
Current Gain-Bandwidth Product	f <sub>T</sub>		130	_	MHz	$I_C = 100$ mA, $V_{CE} = 10$ V, $f = 50$ MHz
Output Capacitance	C <sub>obo</sub>		45		pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times	t <sub>on</sub> t <sub>off</sub>		45 1100	_	ns	$I_{C} = 1A, I_{B1} = 100mA$ $I_{B2} = 100mA, V_{CC} = 10V$

Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ 

#### **Typical Characteristics** @T<sub>amb</sub> = 25°C unless otherwise specified

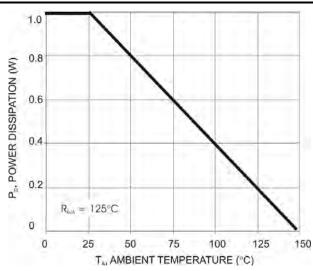


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

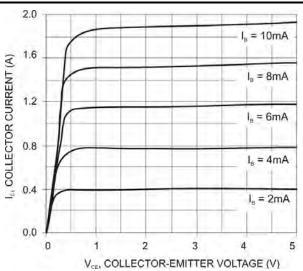


Fig. 2 Collector Current vs. Collector Emitter Voltage



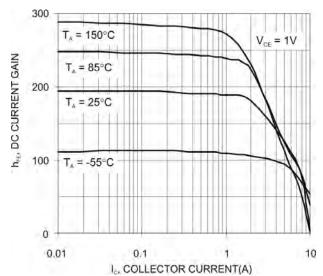


Fig. 3 Typical DC Current Gain vs. Collector Current

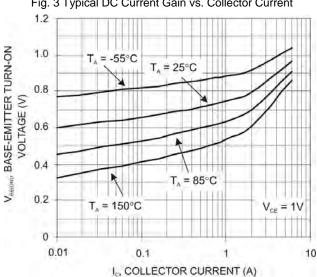


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

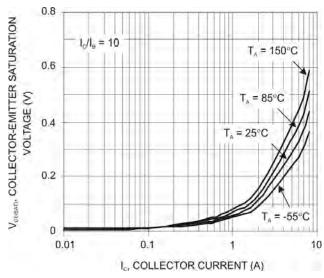


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

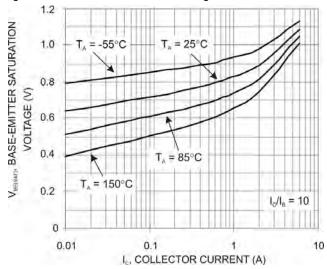


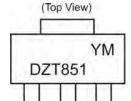
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

### Ordering Information (Note 5)

Device	Packaging	Shipping		
DZT851-13	SOT-223	2500/Tape & Reel		

5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

# **Marking Information**



DZT851 = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006

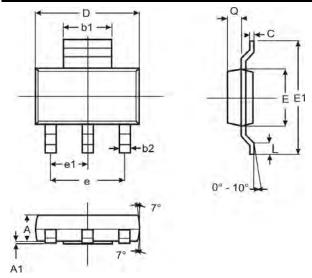
M = Month ex: 9 = September

Year	2006	6	2007	2008 2009 2010			2011		2012			
Code	Т		U		V	V	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

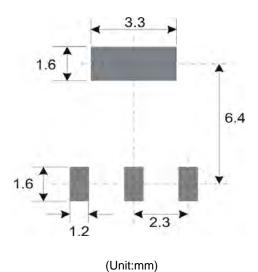


## **Package Outline Dimensions**



SOT-223								
Dim	Min	Max	Тур					
Α	1.55	1.65	1.60					
<b>A</b> 1	0.010	0.15	0.05					
b1	2.90	3.10	3.00					
b2	0.60	0.80	0.70					
С	0.20	0.30	0.25					
D	6.45	6.55	6.50					
E	3.45	3.55	3.50					
E1	6.90	7.10	7.00					
е			4.60					
e1	_		2.30					
L	0.85	1.05	0.95					
Q	0.84	0.94	0.89					
All Dimensions in mm								

# Suggested Pad Layout: (Based on IPC-SM-782)



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